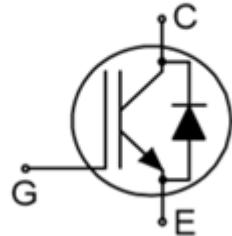


Trench Field-Stop Technology IGBT

Features

- 1200V, 15A
- $V_{CE(sat)(typ.)} = 2.00V @ V_{GE}=15V, I_C=15A$
- Low Switching Losses
- $V_{CE(sat)}$ with Positive Temperature Coefficient
- Pb-free Lead Plating; RoHS Compliant
-



Applications

- Frequency Converters
- Uninterrupted Power Supply
- Air Conditioning
- Motor Drives



Absolute Maximum Ratings

Symbol	Parameter	Value	Unit
V_{CES}	Collector-Emitter Voltage	1200	V
V_{GES}	Gate-Emitter Voltage	± 20	V
I_C	Continuous Collector Current ($T_c=25^\circ\text{C}$)	30	A
	Continuous Collector Current ($T_c=100^\circ\text{C}$)	15	A
I_{CM}	Pulsed Collector Current (Note 1)	45	A
I_F	Diode Continuous Forward Current ($T_c=100^\circ\text{C}$)	15	A
I_{FM}	Diode Maximum Forward Current (Note 1)	45	A
t_{sc}	Short Circuit Withstand Time	10	us
P_D	Maximum Power Dissipation ($T_c=25^\circ\text{C}$)	245	W
	Maximum Power Dissipation ($T_c=100^\circ\text{C}$)	122	W
T_J	Operating Junction Temperature Range	-40 to 175	$^\circ\text{C}$
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$

Thermal Data

Symbol	Parameter	Max.	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case for IGBT	0.61	$^\circ\text{C}/\text{W}$
$R_{\theta DC}$	Thermal Resistance, Junction to Case for Diode	0.77	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	40	$^\circ\text{C}/\text{W}$

Electrical Characteristics ($T_c=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{CES}	Collector-Emitter Breakdown Voltage	$V_{GE}=0\text{V}$, $I_C=500\mu\text{A}$	1200	---	---	V
I_{CES}	Collector-Emitter Leakage Current	$V_{CE}=1200\text{V}$, $V_{GE}=0\text{V}$	---	---	1	mA
I_{GES}	Gate Leakage Current, Forward	$V_{GE}=20\text{V}$, $V_{CE}=0\text{V}$	---	---	400	nA
	Gate Leakage Current, Reverse	$V_{GE}=-20\text{V}$, $V_{CE}=0\text{V}$	---	---	-400	nA
$V_{GE(\text{th})}$	Gate Threshold Voltage	$V_{GE}=V_{CE}$, $I_C=480\mu\text{A}$	5.2	5.8	6.4	V
$V_{CE(\text{sat})}$	Collector-Emitter Saturation Voltage	$V_{GE}=15\text{V}$, $I_C=15\text{A}$	---	2.0	2.25	V
Q_G	Total Gate Charge	$V_{CC}=960\text{V}$ $V_{GE}=15\text{V}$ $I_C=15\text{A}$	---	68	---	nC
Q_{GE}	Gate-Emitter Charge		---	12.8	---	nC
Q_{GC}	Gate-Collector Charge		---	50.2	---	nC
$t_{d(on)}$	Turn-on Delay Time	$V_{CC}=600\text{V}$ $V_{GE}=\pm 15\text{V}$ $I_C=15\text{A}$ $R_G=39\Omega$ Inductive Load $T_c=25^\circ\text{C}$	---	36	---	ns
t_r	Turn-on Rise Time		---	28	---	ns
$t_{d(off)}$	Turn-off Delay Time		---	215	---	ns
t_f	Turn-off Fall Time		---	226	---	ns
E_{on}	Turn-on Switching Loss		---	1.62	---	mJ
E_{off}	Turn-off Switching Loss		---	1.11	---	mJ
E_{ts}	Total Switching Loss		---	2.73	---	mJ
C_{ies}	Input Capacitance	$V_{CE}=25\text{V}$ $V_{GE}=0\text{V}$ $f=1\text{MHz}$	---	903	---	pF
C_{oes}	Output Capacitance		---	94	---	pF
C_{res}	Reverse Transfer Capacitance		---	48	---	pF

Diode Characteristics ($T_c=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
V_F	Diode Forward Voltage	$I_F=15\text{A}$	---	2.6	3.2	V
t_{rr}	Diode Reverse Recovery Time	$V_{CE}=600\text{V}$ $I_F=15\text{A}$ $dI_F/dt=450\text{A}/\mu\text{s}$	---	131.5	---	ns
I_{rr}	Diode Peak Reverse Recovery Current		---	7.2	---	A
Q_{rr}	Diode Reverse Recovery Charge		---	466	---	nC

Note 1: Repetitive Rating: Pulse width limited by maximum junction temperature

Typical Characteristics

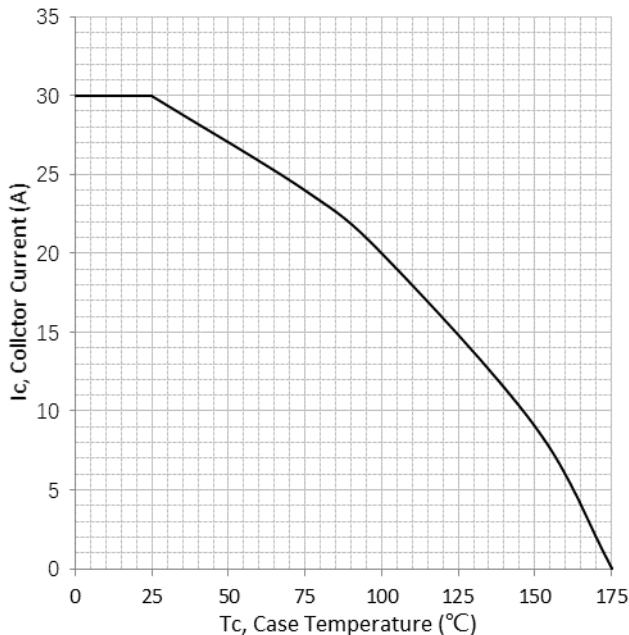


Fig. 1 Maximum DC Collector Current vs. Case Temperature

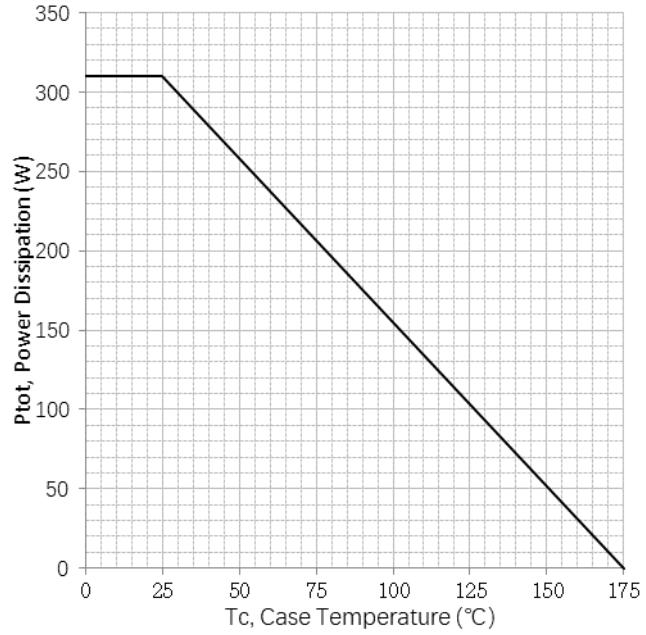


Fig. 2 Power Dissipation vs. Case Temperature

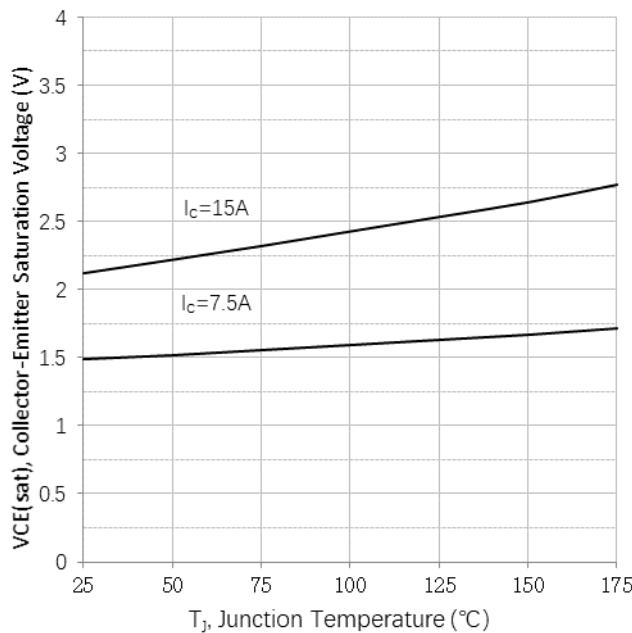


Fig. 3 Typical Collector-Emitter Saturation Voltage vs. Junction Temperature ($V_{GE}=15V$)

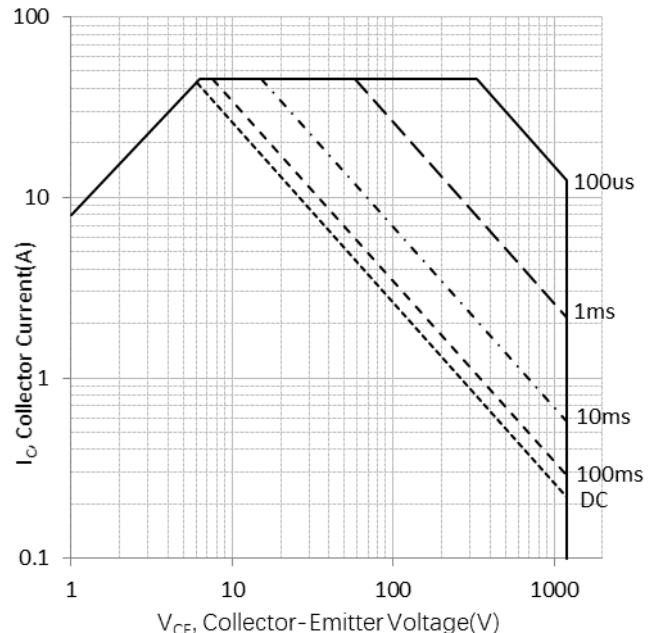


Fig. 4 Safe Operating Area at $T_c=25^\circ C$ and $T_j \leq 175^\circ C$

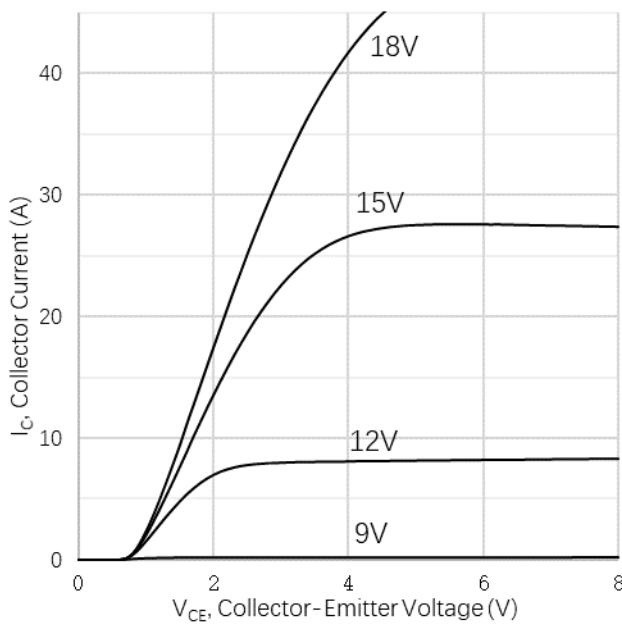


Fig. 5 Typical IGBT Output Characteristics at $T_J=25^\circ\text{C}$

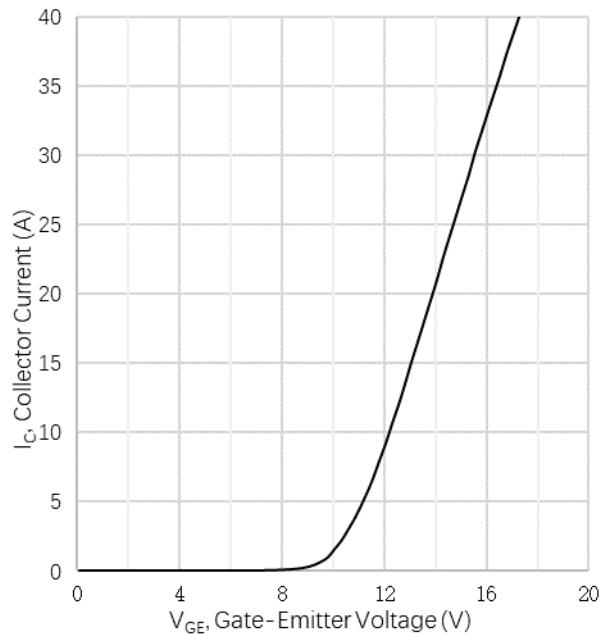


Fig. 6 Typical Transfer Characteristics at $V_{CE}=20\text{V}$

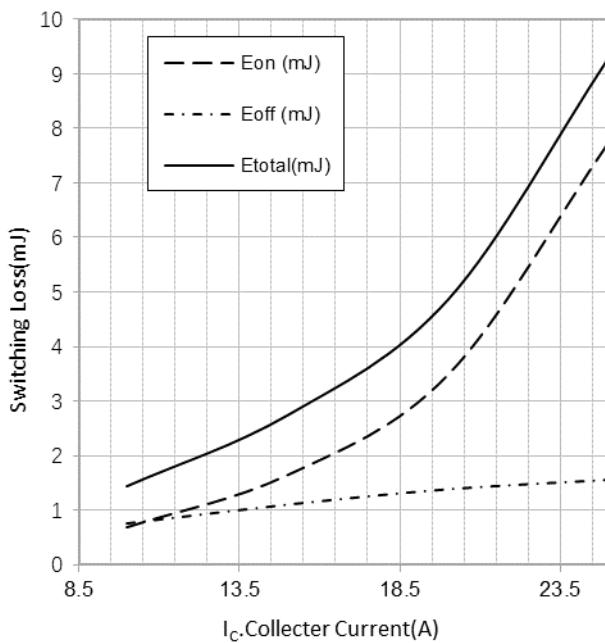


Fig. 7 Typical Energy Loss vs. I_c at $T_c=25^\circ\text{C}$, $V_{CE}=600\text{V}$, $V_{GE}=\pm 15\text{V}$ and $R_g=39\Omega$

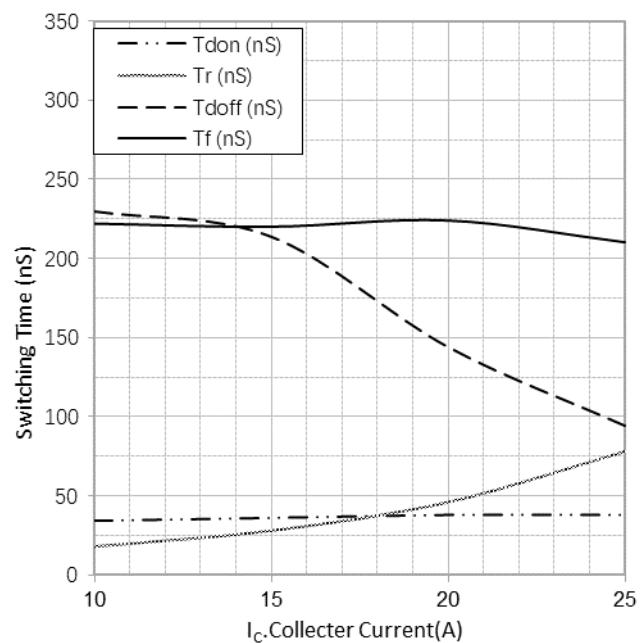
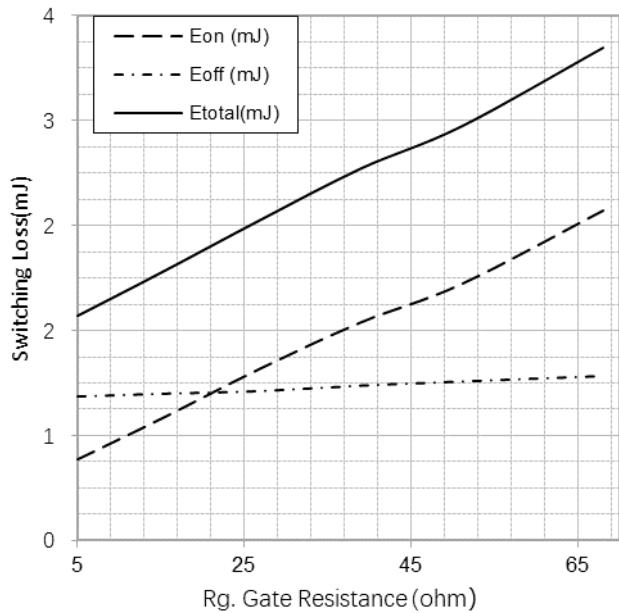
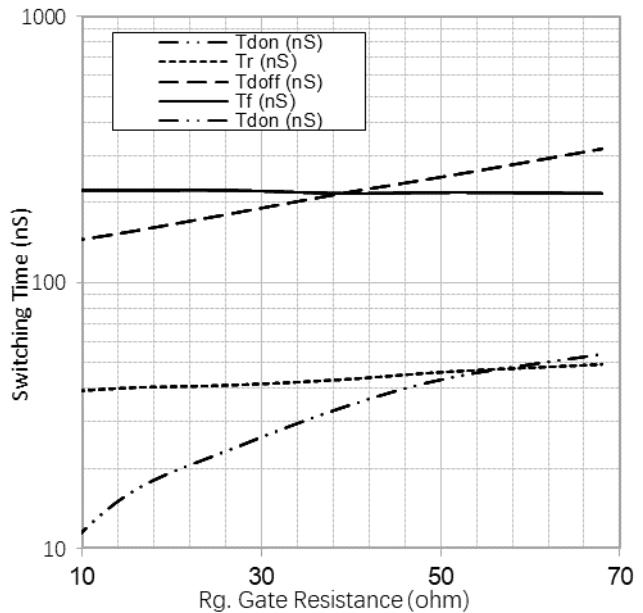


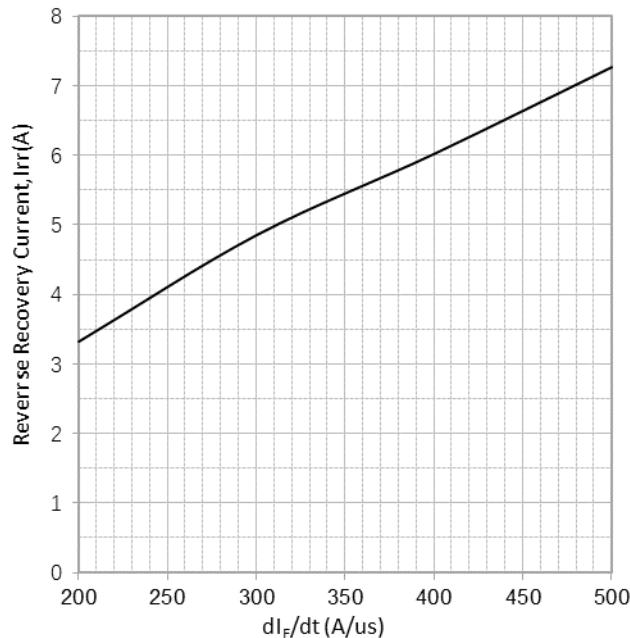
Fig. 8 Typical Switching Time vs. I_c at $T_c=25^\circ\text{C}$, $V_{CE}=600\text{V}$, $V_{GE}=\pm 15\text{V}$ and $R_g=39\Omega$



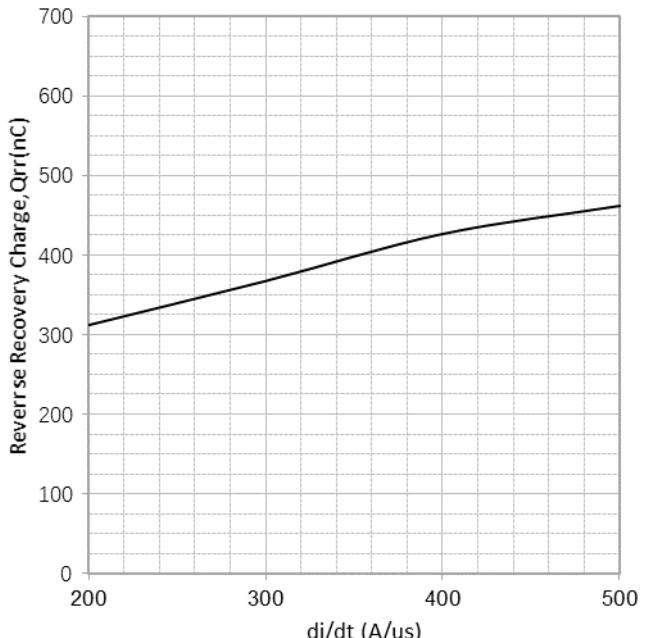
**Fig. 9 Typical Energy Loss vs. Rg at $T_c=25^\circ\text{C}$,
 $V_{CE}=600\text{V}$, $V_{GE}=15\text{V}$, $I_C=15\text{A}$ and $R_g=39\Omega$**



**Fig. 10 Typical Switching Time vs. Rg at $T_c=25^\circ\text{C}$,
 $V_{CE}=600\text{V}$, $V_{GE}=15\text{V}$, $I_C=15\text{A}$ and $R_g=39\Omega$**



**Fig. 11 Typical Diode Irr vs. dI_F/dt at $V_{CC}=600\text{V}$ and
 $V_F=15\text{A}$**



**Fig. 12 Typical Diode Qrr vs. dI_F/dt at $V_{CC}=600\text{V}$ and
 $V_F=15\text{A}$**

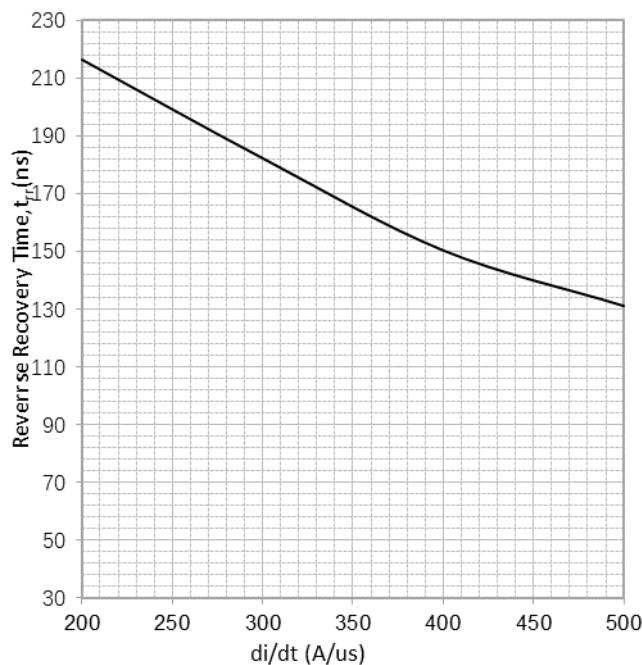


Fig. 13 Typical Diode t_{rr} vs. di_F/dt at $V_{CC}=600V$ and
 $V_F=15A$

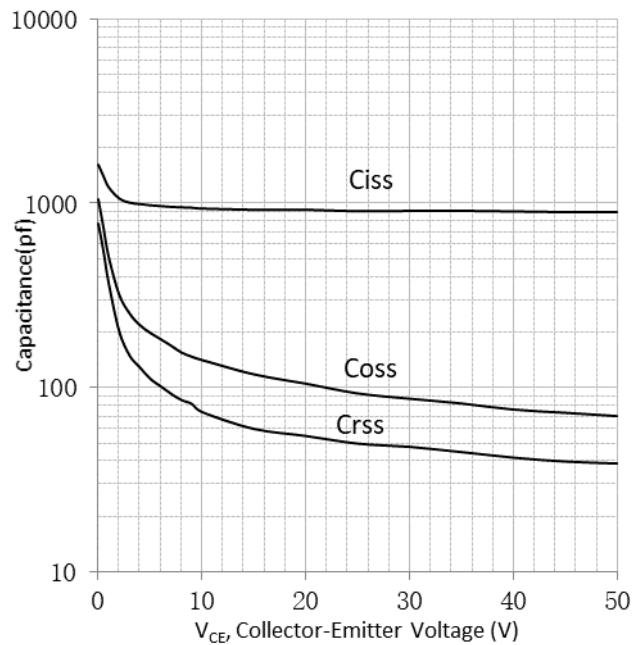


Fig. 14 Typical Capacitance vs. V_{CE} at $V_{GE}=0V$
and $f=1MHz$

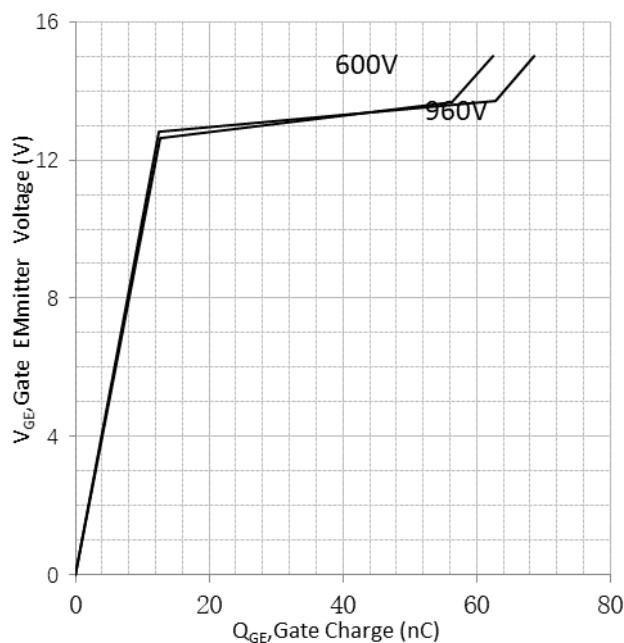


Fig. 15 Typical Gate Charge vs. V_{GE} at $I_C=15A$

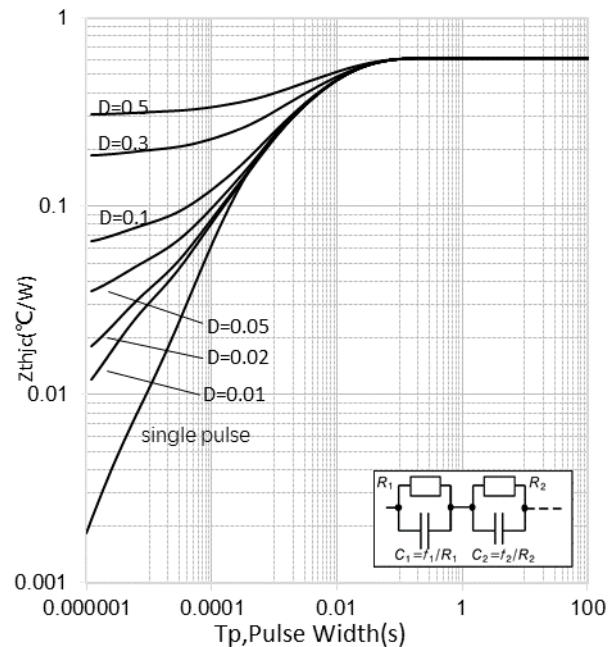
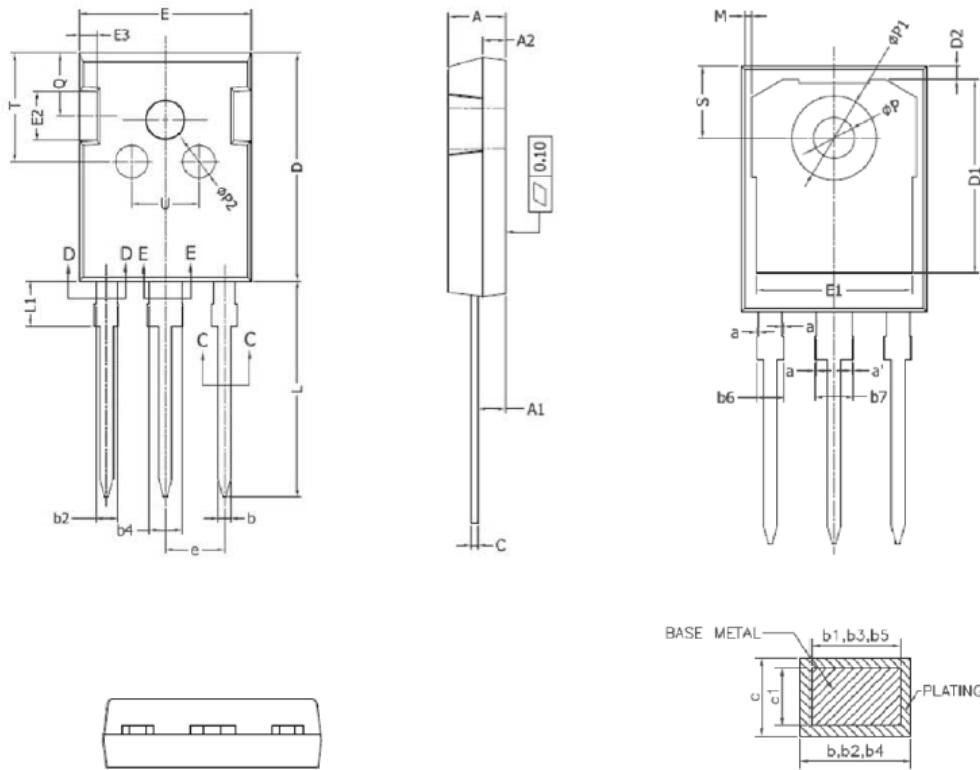


Fig. 16 IGBT Transient Thermal Resistance
($D=t_p / T$)

Package Information

TO-247



COMMON DIMENSIONS
(UNITS OF MEASURE =MILLIMETER)

SYMBOL	MIN	NOM	MAX
A	4.90	5.00	5.10
A1	2.31	2.41	2.51
A2	1.90	2.00	2.10
a	0	—	0.15
a'	0	—	0.15
b	1.16	—	1.26
b1	1.15	1.2	1.22
b2	1.96	—	2.06
b3	1.95	2.00	2.02
b4	2.96	—	3.06
b5	2.96	3.00	3.02
b6	—	—	2.25
b7	—	—	3.25
c	0.59	—	0.66
c1	0.58	0.60	0.62
D	20.90	21.00	21.10
D1	16.25	16.55	16.85
D2	1.05	1.17	1.35
E	15.70	15.80	15.90
E1	13.10	13.30	13.50
E2	4.40	4.50	4.60
E3	1.50	1.60	1.70
e	5.436 BSC		
L	19.80	19.92	20.10
L1	—	—	4.30
M	0.35	—	0.95
P	3.40	3.50	3.60
P1	7.00	—	7.40
P2	2.40	2.50	2.60
Q	5.60	—	6.00
S	6.05	6.15	6.25
T	9.80	—	10.20
U	6.00	—	6.40

NOTES:

ALL DIMENSIONS REFER TO JEDEC STANDARD TO-247 AND DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS.

EJECTION MARK DEPTH $0.10^{+0.15}_{-0.10}$

Revision History

Ver.	Date	Change Notice
1.0	2020/10/11	Released

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[IXGK50N60B](#) [NRND](#) [FGH60N60SMD_F085](#) [NGB8206ANSL3G](#) [IKW20N60H3FKSA1](#) [IKP30N65H5XKSA1](#) [IGA03N120H2XKSA1](#)
[IKW25N120T2FKSA1](#) [IKW15T120FKSA1](#) [IKP20N60TXKSA1](#) [IHW40N65R5XKSA1](#) [IHW20N65R5XKSA1](#) [IGW25T120FKSA1](#)
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[STGB10NB37LZT4](#)